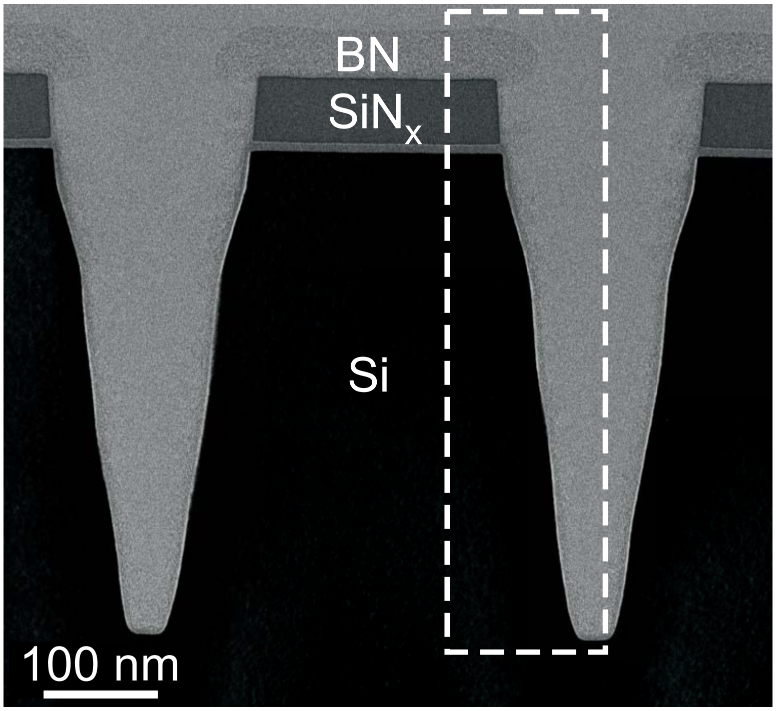

Figure S1: STEM of BN EE-ALD on a patterned wafer. 1000 EE-ALD cycles at 27 °C. 400 eV electron beam at 100 μA for 240 s. Borazine exposure was 7×10^{-2} Torr·s.

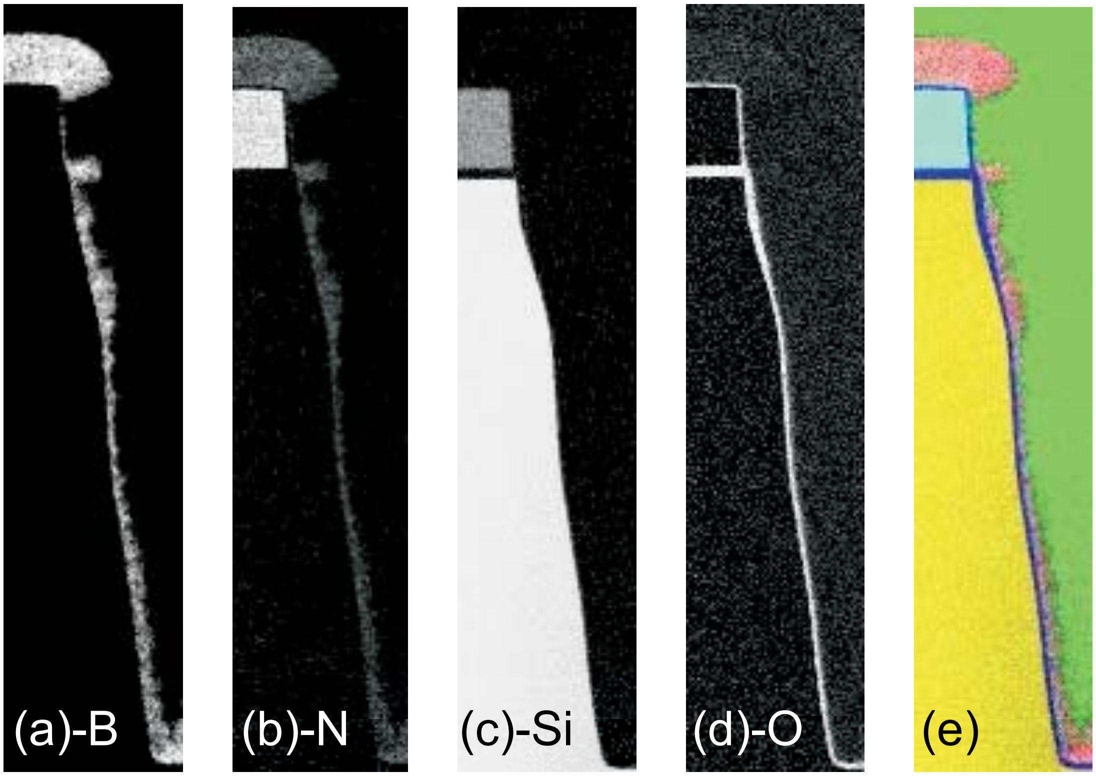

Figure S2: STEM/EELS elemental maps of the region highlighted (dashed) in Figure S1, a-d) B, N, Si, O and e) a false color composite image of the data in Figures S2 a-d.